



<b>PCN Number:</b>	20170621002	<b>PCN Date:</b>	June 22, 2017																
<b>Title:</b>	Qualification of TI Chengdu BUMP (CBUMP) as an Additional Bump and TI Chengdu A/T (CDAT) as an Assembly site for the Select Devices																		
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>	<b>Dept:</b>	Quality Services																
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Sept 22, 2017	<b>Estimated Sample Availability:</b>	Provided upon Request																
<b>Change Type:</b>																			
<input checked="" type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process																
<input type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification																
<input checked="" type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling																
<input checked="" type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material																
<input type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials																
		<input type="checkbox"/>	Part number change																
<b>PCN Details</b>																			
<b>Description of Change:</b>																			
Texas Instruments is pleased to announce the qualification of TI Chengdu BUMP (CBUMP) as an Additional Bump and TI Chengdu A/T (CDAT) as an additional Assembly site for the devices listed in the table below. There is no construction differences in devices built between the various sites.																			
<b>Reason for Change:</b>																			
Continuity of Supply																			
<b>Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):</b>																			
None																			
<b>Anticipated impact on Material Declaration</b>																			
<input checked="" type="checkbox"/>	No Impact to the Material Declaration	<input type="checkbox"/>	Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <a href="#">TI ECO website</a> .																
<b>Changes to product identification resulting from this PCN:</b>																			
<table border="1"> <thead> <tr> <th>Assembly Site</th> <th>Assembly Site Origin (22L)</th> <th>Assembly Country Code (21L)</th> <th>Assembly City</th> </tr> </thead> <tbody> <tr> <td>JCAP</td> <td>JCP</td> <td>CHN</td> <td>Jiangyin</td> </tr> <tr> <td>TI Clark</td> <td>QAB</td> <td>PHL</td> <td>Angeles City, Pampanga</td> </tr> <tr> <td><b>CDAT</b></td> <td><b>CDA</b></td> <td><b>CHN</b></td> <td><b>Chengdu</b></td> </tr> </tbody> </table>				Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (21L)	Assembly City	JCAP	JCP	CHN	Jiangyin	TI Clark	QAB	PHL	Angeles City, Pampanga	<b>CDAT</b>	<b>CDA</b>	<b>CHN</b>	<b>Chengdu</b>
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JCAP	JCP	CHN	Jiangyin																
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<b>CDAT</b>	<b>CDA</b>	<b>CHN</b>	<b>Chengdu</b>																
Sample product shipping label (not actual product label)																			
  <p> (1P) SN74LS07NSR  (Q) 2000 (D) 0336  (31T) LOT: 3959047MLA  (4W) TKY (1T) 7523483SI2  (P)  (2P) REV: (V) 0033317  (20L) CSO: SHE (21L) CCO: USA  (22L) ASO: MLA (23L) ACO: MYS </p> <p> MSL 2 /260C/1 YEAR SEAL DT  MSL 1 /235C/UNLIM 03/29/04  OPT:  ITEM: 39  LBL: 5A (L)T0:1750 </p>																			

**Topside Device marking (if included):**

Assembly site code for QAB= I

Assembly site code for JCP= P

**Assembly site code for CDA = 8****Product Affected**

DRV2605YZFR

DRV2605YZFT

**Qualification Data**

Chengdu BUMP (CBUMP) start -up for BOPCOA -PHASE 1A (DRV2605YZFR)

**Product Attributes**

Attributes	Qual Device: DRV2605YZFR
Assembly Site	CHENGDU A/T
Package Family	DSBGA
Flammability Rating	UL 94 V-0
Wafer Fab Supplier	RFAB
Wafer Fab Process	LBC8LV

- QBS: Qual by Similarity

- Qual Device DRV2605YZFR is qualified at LEVEL1-260C

**Qualification Results Expected**

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: DRV2605YZFR
BLR	BLR - Drop test	30 times	08-15-2017
BLR	BLR - Temp Cycle, -40C / +125C	1000 Cycles	08-15-2017
`ED	Electrical Characterization, side by side	Per Datasheet Parameters	08-15-2017
HAST	Biased HAST, 130C/85%RH	96 Hours	08-15-2017
HBM	ESD HBM	2000V	08-15-2017
HTOL	High Temp Operating Life, 140C	480 Hours	08-15-2017
HTSL	High Temp. Storage Bake, 170C	420 Hours	08-15-2017
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass
MQ	Manufacturability (Bump)	(per mfg. Site specification)	Pass
PD	Physical Dimensions	(per mechanical drawing)	3/15/0
SBS	Bump-shear	unstressed	3/90/0
TC	T/C -55C/125C	700 Cycles	3/231/0
UHAST	Unbiased HAST, 130C/85%RH	96 Hours	3/231/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles  
Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

**Green/Pb-free Status:**

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

<b>Location</b>	<b>E-Mail</b>
USA	<a href="mailto:PCNAmericasContact@list.ti.com">PCNAmericasContact@list.ti.com</a>
Europe	<a href="mailto:PCNEuropeContact@list.ti.com">PCNEuropeContact@list.ti.com</a>
Asia Pacific	<a href="mailto:PCNAsiaContact@list.ti.com">PCNAsiaContact@list.ti.com</a>
Japan	<a href="mailto:PCNJapanContact@list.ti.com">PCNJapanContact@list.ti.com</a>